



7MHz, Precision, Rail-to-Rail I/O CMOS Operational Amplifier

1 Features

- Gain Bandwidth:7MHz
- Rail-to-Rail Input and Output ±0.5mV Max Vos
- Input Voltage Range: -0.1V to +5.6V with Vs = 5.5V
- Supply Range: +2.5V to +5.5V
- Specified Up To +125°C
- Micro Size Packages: SOT23-5, SOT353(SC70-5)

2 Applications

- Sensors
- Photodiode Amplification
- Active Filter
- Test Equipment
- Driving A/D Converters

3 Descriptions

The ZM621P, ZM622P, ZM624P families of products offer low voltage operation and rail-to-rail input and output, as well as excellent speed/power consumption ratio, providing an excellent bandwidth (7MHz) and slew rate of 3.7V/us. The op-amps are unity gain stable and feature an ultra-low input bias current.

The devices are ideal for sensor interfaces, active filters and portable applications. The ZM621P, ZM622P, ZM624P families of operational amplifiers are specified at the full temperature range of -40°C to +125°C under single or dual power supplies of 2.5V to 5.5V.

Bottoo information				
PART NUMBER	PACKAGE	BODY SIZE(NOM)		
71400410	SOT23-5	2.90mm×1.60mm		
ZM621P	SOT353(SC70-5)	2.10mm×1.25mm		
	SOIC-8(SOP8)	4.90mm×3.90mm		
740000	MSOP-8	3.00mm×3.00mm		
ZM622P	TSSOP-8	3.00mm×4.40mm		
	DFN2×2-8L	2.00mm×2.00mm		
	SOIC-14(SOP14)	8.65mm×3.90mm		
ZM624P	TSSOP-14	5.00mm×4.40mm		

Device Information⁽¹⁾

(1) For all available packages, see the orderable addendum at the end of the data sheet.

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4 Revision History

Note: Page numbers for previous revisions may different from page numbers in the current version.

VERSION	Change Date	Change Item
A.1	2021/11/11	Initial version completed

5 Package/Ordering Information⁽¹⁾

Orderable Device	Package Type	Pin	Channel	Op Temp(°C)	Device Marking ⁽²⁾	MSL ⁽³⁾	Package Qty
ZM621PXF	SOT23-5	5	1	-40℃~125℃	621P	MSL3	Tape and Reel,3000
ZM621PXC5	SOT353(SC70-5)	5	1	-40℃~125℃	621P	MSL3	Tape and Reel,3000
ZM621BPXF	SOT23-5	5	1	-40℃~125℃	621BP	MSL3	Tape and Reel,3000
ZM621BPXC5	SOT353(SC70-5)	5	1	-40℃~125℃	621BP	MSL3	Tape and Reel,3000
ZM622PXK	SOIC-8(SOP8)	8	2	-40℃~125℃	ZM622P	MSL3	Tape and Reel,4000
ZM622PXM	MSOP-8	8	2	-40℃~125℃	ZM622P	MSL3	Tape and Reel,4000
ZM622PXQ	TSSOP-8	8	2	-40℃~125℃	ZM622P	MSL3	Tape and Reel,4000
ZM622PXTDE8	DFN2X2-8	8	2	-40℃~125℃	ZM622P	MSL3	Tape and Reel,3000
ZM624PXP	SOIC-14(SOP14)	14	4	-40℃~125℃	ZM624P	MSL3	Tape and Reel,4000
ZM624PXQ	TSSOP-14	14	4	-40°C~125°C	ZM624P	MSL3	Tape and Reel,4000

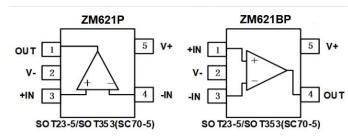
NOTE:

(1) This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the right-hand navigation.

(2) There may be additional marking, which relates to the lot trace code information (data code and vendor code), the logo or the environmental category on the device.

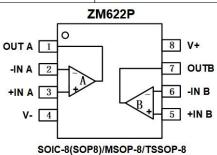
(3) MSL, The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications.

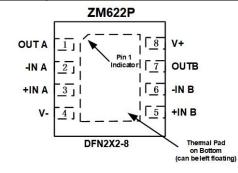
6 Pin Configuration and Functions (Top View)



Pin Description

	F	PIN				
NAME	ZM621P	ZM621BP	I/O	DESCRIPTION		
	SOT23-5/ SOT23-5/ SOT353(SC70-5) SOT353(SC70-5)					
-IN	4 3		I	Negative (inverting) input		
+IN	3	1	I	Positive (noninverting) input		
OUT	1 4		0	Output		
V-	2 2		-	Negative (lowest) power supply		
V+	5 5		-	Positive (highest) power supply		

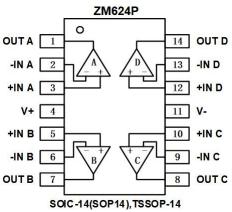




Pin Description

NAM	NAM PIN E SOIC-8(SOP8)/MSOP-8/TSSOP-8/DFN2X2-8		PIN I/O		DESCRIPTION
E			DESCRIPTION		
-INA	2	I	Inverting input, channel A		
+INA	3	I	Noninverting input, channel A		
-INB	6	I	Inverting input, channel B		
+INB	5	I	Noninverting input, channel B		
OUTA	1	0	Output, channel A		
OUTB	7	0	Output, channel B		
V-	4	-	Negative (lowest) power supply		
V+	8	-	Positive (highest) power supply		

Pin Configuration and Functions (Top View)



Pin Description

NAME	PIN	I/O	DESCRIPTION			
NAME	SOIC-14(SOP14)/TSSOP-14		DESCRIPTION			
-INA	2	I	Inverting input, channel A			
+INA	3	I	Noninverting input, channel A			
-INB	6	I	Inverting input, channel B			
+INB	5	I	Noninverting input, channel B			
-INC	9	I	Inverting input, channel C			
+INC	10	I	Noninverting input, channel C			
-IND	13	I	Inverting input, channel D			
+IND	12	I	Noninverting input, channel D			
OUTA	1	0	Output, channel A			
OUTB	7	0	Output, channel B			
OUTC	8	0	Output, channel C			
OUTD	14	0	Output, channel D			
V-	11	-	Negative (lowest) power supply			
V+	4	-	Positive (highest) power supply			

7 Specifications

7.1 Absolute Maximum Ratings

Over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

			MIN	MAX	UNIT	
	Supply, Vs=(V+) - (V-)	V+) - (V-)		7		
Voltage	Signal input pin ⁽²⁾		(V-)-0.5	(V+) +0.5	V	
	Signal output pin ⁽³⁾		(V-)-0.5	(V+) +0.5		
	Signal input pin ⁽²⁾		-10	10	mA	
Current	Signal output pin ⁽³⁾		-140	140	mA	
	Output short-circuit (4)		Conti	nuous		
		SOT23-5		230		
	Package thermal impedance ⁽⁵⁾	SOIC-8(SOP8)		110	- - - °C/W	
		MSOP-8		170		
θ _{JA}		TSSOP-8		240		
0JA		SOIC-14(SOP14)		105		
		TSSOP14		90		
		SC70-5		380		
		DFN2X2-8		80		
	Operating range, T _A		-40	125		
Temperature	Junction, T _J			150	°C	
	Storage, T _{stg}		-65	150	1	

(1)Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

(2)Input terminals are diode-clamped to the power-supply rails. Input signals that can swing more than 0.5V beyond the supply rails should be current-limited to 10mA or less.

(3)Output terminals are diode-clamped to the power-supply rails. Output signals that can swing more than 0.5V beyond the supply rails should be current-limited to ±50mA or less.

(4)Short-circuit to ground, one amplifier per package.

(5)The package thermal impedance is calculated in accordance with JESD-51.

(6) The maximum power dissipation is a function of $T_{J(MAX)}$, R_{0JA} , and T_A . The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(MAX)} - T_A) / R_{0JA}$. All numbers apply for packages soldered directly onto a PCB.

7.2 ESD Ratings

The following ESD information is provided for handling of ESD-sensitive devices in an ESD protected area only.

			VALUE	UNIT
V	Electrostatic discharge	Human-body model (HBM)	±3000	V
V(ESD)	Electrostatic discriarge	Machine Model (MM)	±200	v



ESD SENSITIVITY CAUTION

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

7.3 Recommended Operating Conditions Over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
Supply voltage, Vs= (V+) - (V-)	Single-supply	2.5		5.5	V
	Dual-supply	±1.25		±2.75	v

7.4 Electrical Characteristics

(At $T_A = +25^{\circ}C$, Vs=5V, $R_L = 10k\Omega$ connected to $V_S/2$, and $V_{OUT} = V_S/2$, $V_{CM} = V_S/2$, Full⁽⁹⁾=-40°C to +125°C, unless otherwise noted.)⁽¹⁾

			_	ZN	ZM621P, ZM622P, ZM624P			
PARAMETER		CONDITIONS	TJ	MIN ⁽²⁾	TYP ⁽³⁾	MAX ⁽²⁾	UNITS	
POWER	SUPPLY							
Vs	Operating Voltage Range		25°C	2.5		5.5	V	
IQ	Quiescent Current/Amplifier	Vs=±2.5V,Io=0mA	25°C		720	1000	μA	
PSRR	Dower Supply Dejection Datio	Vs=2.5V to 5.5V,	25°C	75	96		٩D	
PORK	Power-Supply Rejection Ratio	V _{CM} =(V-)+0.5V	Full	67			dB	
t _{ON}	Turn-on Time		25°C		12		μs	
INPUT		·		·				
Vos	Input Offset Voltage	V _{см} =V _s /2	25°C	-0.5	±0.3	0.5	mV	
Vos Tc	Input offset voltage drift	V _{CM} =V _S /2	Full		±2.0		μV/°C	
IB	Input Bias Current ⁽⁴⁾⁽⁵⁾	V _{CM} =0	25°C		±1	±10	pА	
los ⁽⁵⁾	Input Offset Current ⁽⁴⁾	V _{CM} =0	25°C		±1	±10	pА	
Vсм	Common-Mode Voltage Range	Vs= 5.5V	25°C	-0.1		5.6	V	
	Common-Mode Rejection Ratio	Vs= 5.5V, 25°C V _{CM} =-0.1V to 4V Full	25°C	75	96		dB	
			Full	65				
CMRR		Vs= 5.5V, V _{CM} = -0.1V to 5.6V	25°C	64	81			
			Full	60				
OUTPU	Г	1			•			
		R _L =10kΩ, Vo=0.015V to 4.985V	25°C	100	110		dB	
A _{OL}	Open-Loop Voltage Gain		Full	87				
	Output Swing From Rail	V _S =±2.5V,R _L =10kΩ	25°C		10		mV	
IOUT	Output Current Source ⁽⁶⁾⁽⁷⁾		25°C		120		mA	
FREQU	ENCY RESPONSE							
SR	Slew Rate ⁽⁸⁾		25°C		3.7		V/µs	
GBP	Gain-Bandwidth Product		25°C		7		MHz	
PM	Phase Margin ⁽⁵⁾		25°C		64		٥	
ts	Setting Time,0.1%		25°C		0.5		μs	
t _{OR}	Overload recovery time	V _{IN} ×G≥V _S ,G=-10	25°C		1		μs	
NOISE								
•	Input Voltage Naiss Dansity	f = 1kHz	25°C		11		nV/√Hz	
en	Input Voltage Noise Density	f = 1kHz	25°C		7.5		nV/√Hz	

(1) Electrical table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device.

(2) Limits are 100% production tested at 25°C. Limits over the operating temperature range are ensured through correlations using statistical quality control (SQC) method.

(3) Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration.

(4) This parameter is ensured by design and/or characterization and is not tested in production.

(5) Positive current corresponds to current flowing into the device.

(6) The maximum power dissipation is a function of TJ(MAX), R θ JA, and TA. The maximum allowable power dissipation at any ambient temperature is PD = (T J(MAX) - TA) / R θ JA. All numbers apply for packages soldered directly onto a PCB.

(7) Short circuit test is a momentary test.

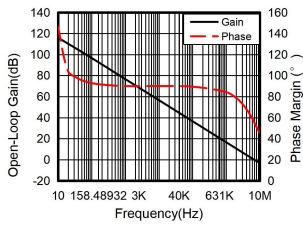
(8) Number specified is the slower of positive and negative slew rates.

(9) Specified by characterization only.

7.5 Typical Characteristics

NOTE: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only.

At T_A = +25°C, Vs=5V, R_L = 10k Ω connected to V_S/2, V_{OUT} = V_S/2, unless otherwise noted.





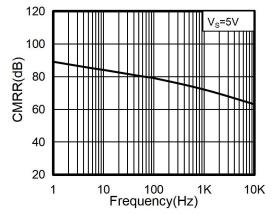
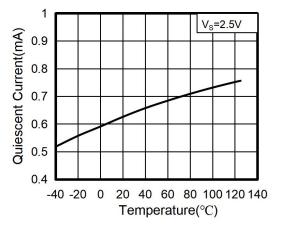


Figure 3. Common-Mode Rejection Ratio vs Frequency





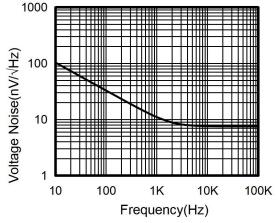


Figure 2. Input Voltage Noise Spectral Density vs Frequency

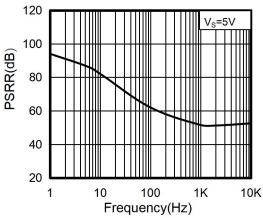


Figure 4. Power-Supply Rejection Ratio vs Frequency

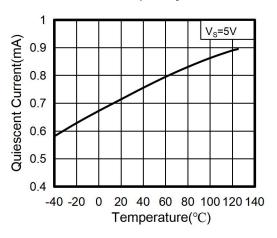


Figure 6. Quiescent Current vs Temperature

Typical Characteristics

NOTE: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only.

At T_A = +25°C, Vs=5V, R_L = 10k Ω connected to V_S/2, V_{OUT} = V_S/2, unless otherwise noted.

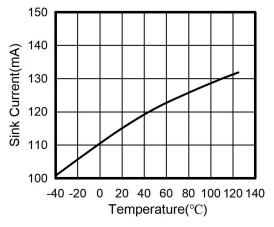


Figure 7. Sink Current vs Temperature

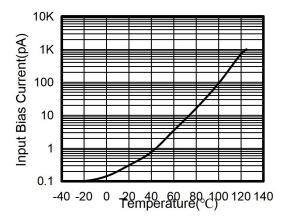


Figure 9. Input Bias Current vs Temperature

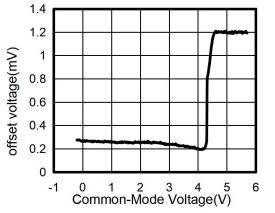


Figure 11. Offset Voltage vs Common-Mode Voltage

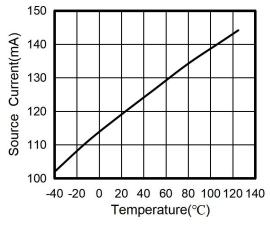


Figure 8. Source Current vs Temperature

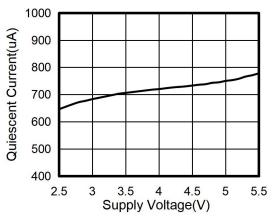


Figure 10. Quiescent Current vs Supply Voltage

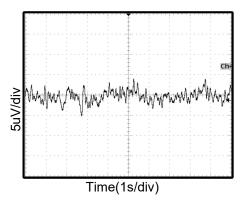


Figure 12. 0.1Hz to 10Hz Input Voltage Noise

Typical Characteristics

NOTE: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only.

At T_A = +25°C, Vs=5V, R_L = 10k Ω connected to Vs/2, V_{OUT} = Vs/2, unless otherwise noted.

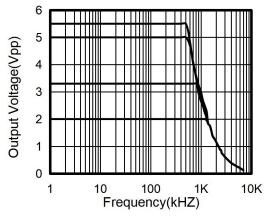


Figure 13. Maximum Output Voltage vs Frequency

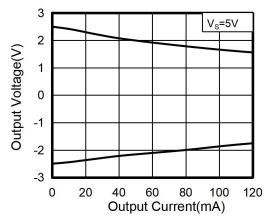
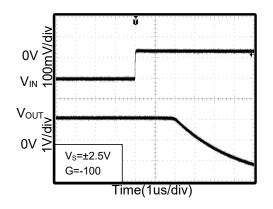
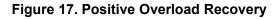


Figure 15. Output Voltage vs Output Current





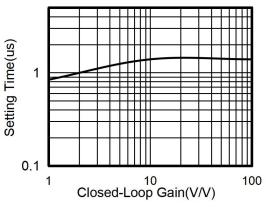


Figure 14. Setting Time vs Closed-loop Gain

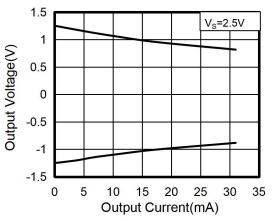


Figure 16. Output Voltage vs Output Current

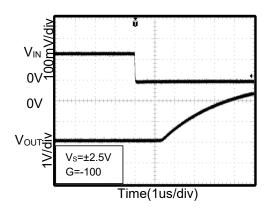
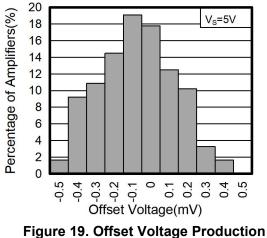


Figure 18. Negative Overload Recovery

Typical Characteristics

NOTE: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only.

At T_A = +25°C, Vs=5V, R_L = 10k Ω connected to Vs/2, V_{OUT} = Vs/2, unless otherwise noted.



Distribution

8 Detailed Description

8.1 Overview

The ZM62XP devices are unity-gain stable, dual and qual-channel op amps with low noise and distortion. The device consists of a low noise input stage with a folded cascade and a rail-to-rail output stage. This topology exhibits superior noise and distortion performance across a wide range of supply voltages that are not delivered by legacy commodity audio operational amplifiers.

8.2 Phase Reversal Protection

The ZM62XP family has internal phase-reversal protection. Many op amps exhibit phase reversal when the input is driven beyond the linear common-mode range. This condition is most often encountered in noninverting circuits when the input is driven beyond the specified common-mode voltage range, causing the output to reverse into the opposite rail. The input of the ZM62XP prevents phase reversal with excessive common-mode voltage. Instead, the appropriate rail limits the output voltage. This performance is shown in figure 20.

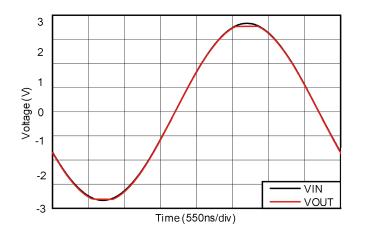


Figure 20. Output Waveform Devoid of Phase Reversal During an Input Overdrive Condition

8.3 EMI Rejection Ratio (EMIRR)

The electromagnetic interference (EMI) rejection ratio, or EMIRR, describes the EMI immunity of operational amplifiers. An adverse effect that is common to many operational amplifiers is a change in the offset voltage as a result of RF signal rectification. An operational amplifier that is more efficient at rejecting this change in offset as a result of EMI has a higher EMIRR and is quantified by a decibel value. Measuring EMIRR can be performed in many ways, but this document provides the EMIRR IN+, which specifically describes the EMIRR performance when the RF signal is applied to the noninverting input pin of the operational amplifier. In general, only the noninverting input is tested for EMIRR for the following three reasons:

• Operational amplifier input pins are known to be the most sensitive to EMI, and typically rectify RF signals better than the supply or output pins.

• The noninverting and inverting operational amplifier inputs have symmetrical physical layouts and exhibit nearly matching EMIRR performance.

• EMIRR is easier to measure on noninverting pins than on other pins because the noninverting input pin can be isolated on a printed-circuit-board (PCB). This isolation allows the RF signal to be applied directly to the noninverting input pin with no complex interactions from other components or connecting PCB traces.

Detailed Description (continued)

The EMIRR IN+ of the ZM62XP is plotted versus frequency in Figure 21. If available, any dual and quad operational amplifier device versions have approximately identical EMIRR IN+ performance. The ZM62XP unity-gain bandwidth is 7MHz. EMIRR performance below this frequency denotes interfering signals that fall within the operational amplifier bandwidth.

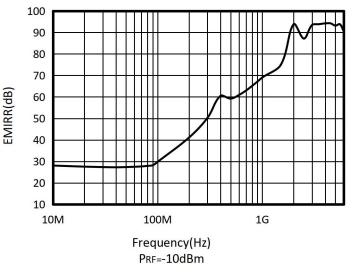


Figure 21. ZM62XP EMIRR vs Frequency

8.4 EMIRR IN+ Test Configuration

Figure 22 shows the circuit configuration for testing the EMIRR IN+. An RF source is connected to the operational amplifier noninverting input pin using a transmission line. The operational amplifier is configured in a unity-gain buffer topology with the output connected to a low-pass filter (LPF) and a digital multimeter (DMM). A large impedance mismatch at the operational amplifier input causes a voltage reflection; however, this effect is characterized and accounted for when determining the EMIRR IN+. The resulting dc offset voltage is sampled and measured by the multimeter. The LPF isolates the multimeter from residual RF signals that can interfere with multimeter accuracy.

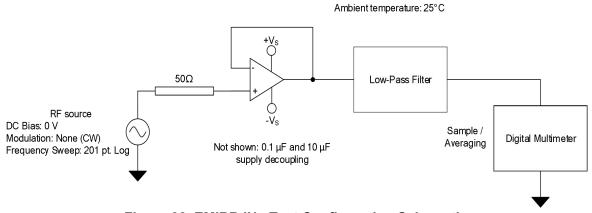


Figure 22. EMIRR IN+ Test Configuration Schematic

9 Application and Implementation

Information in the following applications sections is not part of the Z-Micro component specification, and Z-Micro does not warrant its accuracy or completeness. Z-Micro's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Note

The ZM62XP series features 7MHz bandwidth and 3.7V/µs slew rate with only 720 µA of supply current per channel, providing good AC performance at low power consumption. DC applications are well served with a low input noise voltage, low input bias current, and a typical input offset voltage of 0.3mV.

Typical Applications 9.2 25-kHz Low-pass Filter

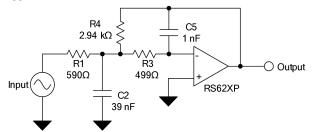


Figure 23. 25-kHz Low-Pass Filter

9.3 Design Requirements

Low-pass filters are commonly employed in signal processing applications to reduce noise and prevent aliasing. The ZM62XP devices are ideally suited to construct high-speed, high-precision active filters. Figure 21 shows a second-order, low-pass filter commonly encountered in signal processing applications. Use the following parameters for this design example:

• Gain = 5 V/V (inverting gain)

- Low-pass cutoff frequency = 25 kHz
- Second-order Chebyshev filter response with 3-dB gain peaking in the passband

9.4 Detailed Design Procedure

The infinite-gain multiple-feedback circuit for a low-pass network function is shown in Figure 21. Use Equation 1 to calculate the voltage transfer function.

$\frac{\text{Output}}{(s)}$	/R ₁ R ₃ C ₂ C ₅
Input	$s^{2} + (s/C_{2}) (1/R_{1} + 1/R_{3} + 1/R_{4}) + 1/R_{3}R_{4}C_{2}C_{5}$

(1) This circuit produces a signal inversion. For this circuit, the gain at dc and the low-pass cutoff frequency are calculated by Equation 2:

$$Gain = \frac{R_4}{R_1}$$
$$f_C = \frac{1}{2\pi} \sqrt{(1/R_3R_4C_2C_5)}$$

(2)

9.5 Application Curve

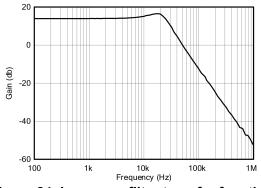


Figure 24. Low-pass filter transfer function

10 Layout

10.1 Layout Guideline

Attention to good layout practices is always recommended. Keep traces short. When possible, use a PCB ground plane with surface-mount components placed as close to the device pins as possible. Place a 0.1uF capacitor closely across the supply pins.

These guidelines should be applied throughout the analog circuit to improve performance and provide benefits such as reducing the EMI susceptibility.

10.2 Layout Example

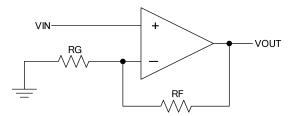


Figure 25. Schematic Representation

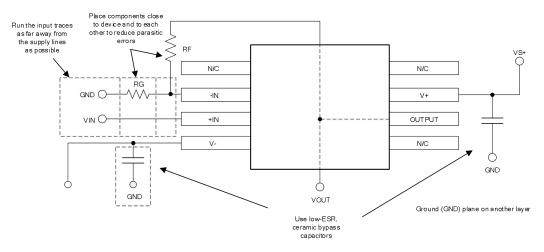
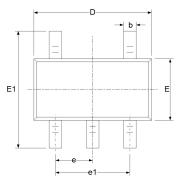
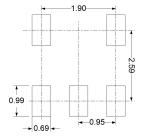


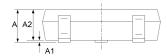
Figure 26. Operational Amplifier Board Layout for Noninverting Configuration

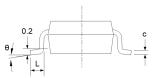
11 Pacakge Outline Dimensions SOT23-5





RECOMMENDED LAND PATTERN (Unit: mm)



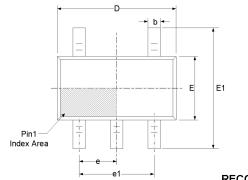


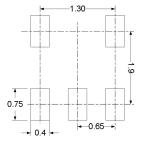
Symbol	Dimensions I	In Millimeters	Dimensions In Inches		
Symbol	Min Max		Min	Max	
A	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
с	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
e	0.950(BSC)		0.037(BSC)		
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	

NOTE:

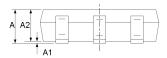


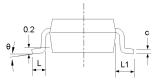
SOT353(SC70-5)





RECOMMENDED LAND PATTERN (Unit: mm)



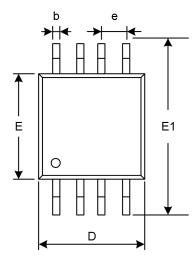


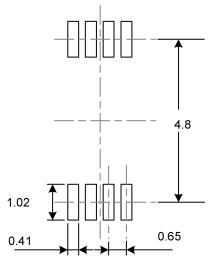
Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
Symbol	Min	Мах	Min	Max	
A	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.150	0.350	0.006	0.014	
с	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
E	1.150	1.350	0.045	0.053	
E1	2.150	2.450	0.085	0.096	
e	0.650(BSC)		0.026	(BSC)	
e1	1.300	1.300(BSC) 0.051(BSC)			
L	0.260	0.460	0.010 0.018		
L1	0.5	0.525)21	
θ	0°	8°	0° 8°		

NOTE:

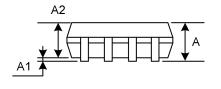
Z-Micro

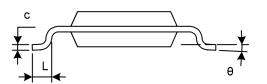
MSOP-8





RECOMMENDED LAND PATTERN (Unit: mm)



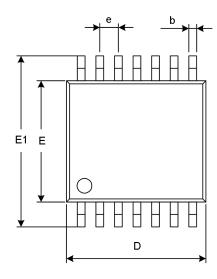


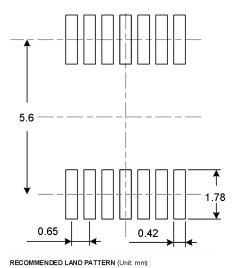
Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
Symbol	Min Max		Min	Max	
A	0.820	1.100	0.032	0.043	
A1	0.020	0.150	0.001	0.006	
A2	0.750	0.950	0.030	0.037	
b	0.250	0.380	0.010	0.015	
с	0.090	0.230	0.004	0.009	
D	2.900	3.100	0.114	0.122	
е	0.650	(BSC)	0.026	(BSC)	
E	2.900	3.100	0.114	0.122	
E1	4.750	5.050	0.187	0.199	
L	0.400	0.800	0.016	0.031	
θ	0°	6°	0°	6°	

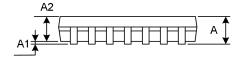
NOTE:

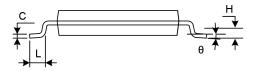
Z-Micro

TSSOP-14







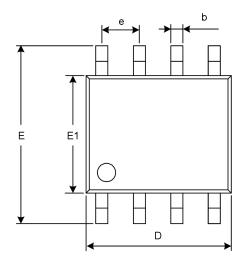


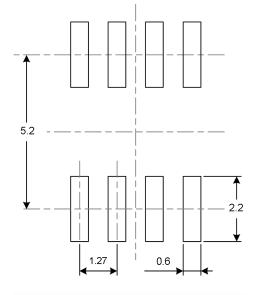
Symbol	Dimensions I	In Millimeters	Dimensions In Inches		
Symbol	Min Max		Min	Мах	
A		1.200		0.047	
A1	0.050	0.150	0.002	0.006	
A2	0.800	1.050	0.031	0.041	
b	0.190	0.300	0.007	0.012	
с	0.090	0.200	0.004	0.008	
D	4.860	5.100	0.191	0.201	
E	4.300	4.500	0.169	0.177	
E1	6.250	6.550	0.246	0.258	
е	0.650(BSC)		0.026(BSC)		
L	0.500	0.700	0.020	0.028	
н	0.25(TYP)	0.01(TYP)	
θ	1°	7°	1° 7°		

NOTE:

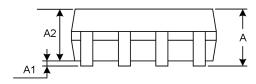
ZM621P,ZM622P,ZM624P

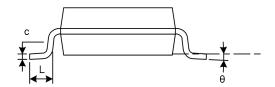
SOIC-8(SOP8)





RECOMMENDED LAND PATTERN (Unit: mm)

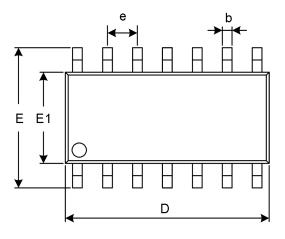


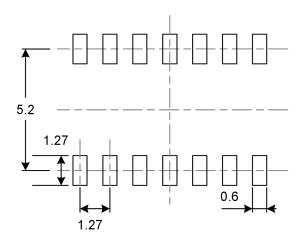


Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
Symbol	Min Max		Min	Max	
A	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
с	0.170	0.250	0.007	0.010	
D	4.800	5.000	0.189	0.197	
е	1.270(BSC)		0.050	(BSC)	
E	5.800	6.200	0.228	0.244	
E1	3.800	4.000	0.150	0.157	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	

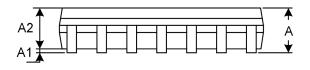
NOTE:

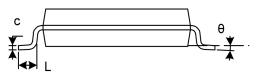
SOIC-14(SOP14)





RECOMMENDED LAND PATTERN (Unit: mm)



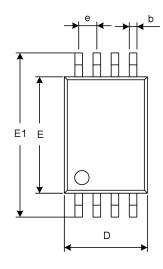


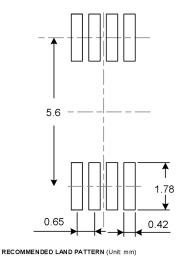
Sumbol	Dimensions	n Millimeters	Dimensions In Inches		
Symbol	Min Max		Min	Max	
А	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.310	0.510	0.012	0.020	
с	0.100	0.250	0.004	0.010	
D	8.450	8.850	0.333	0.348	
е	1.270(BSC)		0.050	(BSC)	
E	5.800	6.200	0.228	0.244	
E1	3.800	4.000	0.150	0.157	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	

NOTE:

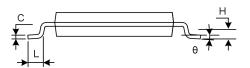
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TSSOP-8





A2 A Ħ A1

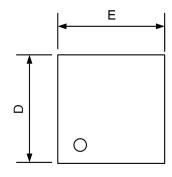


Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
Symbol	Min	Min Max		Max	
A		1.200		0.047	
A1	0.050	0.150	0.002	0.006	
A2	0.800	1.050	0.031	0.041	
b	0.190	0.300	0.007	0.012	
с	0.090	0.200	0.004	0.008	
D	2.900	3.100	0.114	0.122	
E	4.300	4.500	0.169	0.177	
E1	6.250	6.550	0.246	0.258	
e	0.650(BSC)		0.026(BSC)		
L	0.500	0.700	0.020	0.028	
Н	0.25(TYP)	0.01(TYP)	
θ	1°	7°	1° 7°		

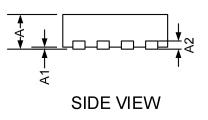
NOTE:

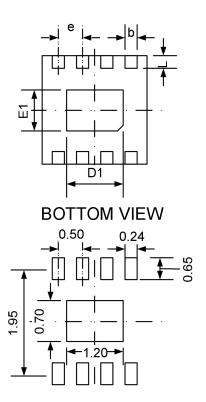
Z-Micro

DFN2X2-8



TOP VIEW





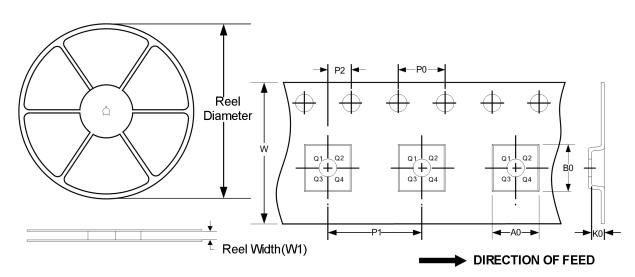
RECOMMENDED LAND PATTERN (Unit: mm)

Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
Symbol	Min Max		Min	Max	
A	0.700	0.800	0.028	0.031	
A1	0.000	0.050	0.000	0.002	
A2	0.203	(TYP)	0.008(TYP)		
b	0.180	0.300	0.007	0.012	
D	1.900	2.100	0.075	0.083	
D1	1.100	1.300	0.043	0.051	
E	1.900	2.100	0.075	0.083	
E1	0.600	0.800	0.024	0.031	
е	0.500(TYP)		0.020	(TYP)	
L	0.250	0.450	0.010	0.018	

NOTE:

12 Tape and Reel Information REEL DIMENSIONS

TAPE DIMENSION



NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF TAPE AND REEL

Package Type	Reel Diameter	Reel Width(mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
SOT23-5	7"	9.5	3.20	3.20	1.40	4.0	4.0	2.0	8.0	Q3
SOIC-8(SOP8)	13"	12.4	6.40	5.40	2.10	4.0	8.0	2.0	12.0	Q1
MSOP-8	13"	12.4	5.20	3.30	1.50	4.0	8.0	2.0	12.0	Q1
SOIC-14(SOP14)	13"	16.4	6.60	9.30	2.10	4.0	8.0	2.0	16.0	Q1
TSSOP-14	13"	12.4	6.95	5.60	1.20	4.0	8.0	2.0	12.0	Q1
SOT353(SC70-5)	7"	9.5	2.25	2.55	1.20	4.0	4.0	2.0	8.0	Q3
DFN2X2-8	7"	9.5	2.30	2.30	1.10	4.0	4.0	2.0	8.0	Q2
TSSOP-8	13"	12.4	6.90	3.45	1.65	4.0	8.0	2.0	12.0	Q1

NOTE:

1. All dimensions are nominal.

2. Plastic or metal protrusions of 0.15mm maximum per side are not included.

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